Silicon NPN Power Transistors 2SD201

DESCRIPTION

·With TO-3 package
·Large current capability
·Wide area of safe operation

APPLICATIONS

·For power amplifier and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	90	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
P_C	Collector power dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA ;I_B=0	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A ; I_B=0.5A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A ; I_B=0.5A			2.5	V
I_{CBO}	Collector cut-off current	V_{CB}=90V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=3A ; V_{CE}=4V	40			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=12V		8		MHz

PACKAGE OUTLINE

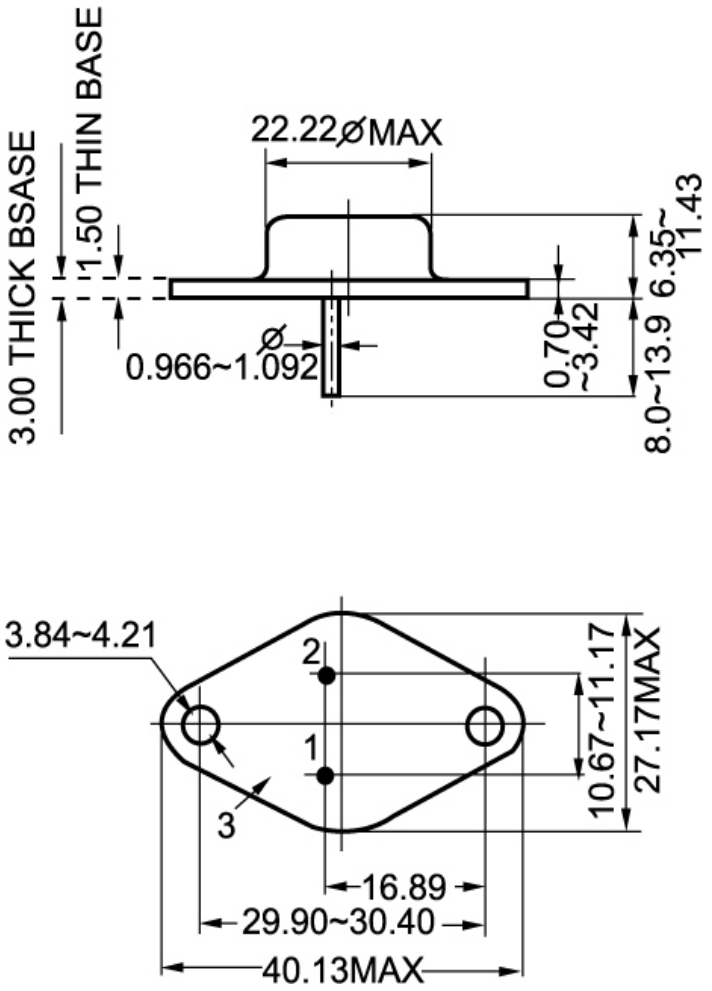

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)